

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Patent No7,105,208 B2
Patent Issue Date September 12, 2006
Application Serial No. 10/699,013
Filing DateOctober 30, 2003
Assignee Micron Technology, Inc.
Inventorship.....Craig M. Carpenter
Attorney's Docket No.MI22-2434
Title: Methods And Processes Utilizing Microwave Excitation

**REQUEST FOR CERTIFICATE OF CORRECTION OF PATENT FOR
APPLICANT MISTAKES and PTO MISTAKES (37 C.F.R. §§ 1.322(a) and 1.323)**

To: Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450
ATTN: Decision and Certificate of Correction
Branch of the Patent Issue Division

From: David G. Latwesen, Ph.D. (Tel. 509-624-4276; Fax 509-838-3424)
Wells St. John P.S.
601 W. First Avenue, Suite 1300
Spokane, WA 99201-3828

Sir:

It is hereby requested that a Certificate of Correction be issued with respect to Patent No. 7,105,208 B2, granted September 12, 2006, in accordance with the Certificate of Correction form attached hereto in duplicate.

It is noted that errors appear in this patent of a typographical nature of character, as more fully described below. The errors occurred in good faith. Correction thereof does not involve such changes in the patent as would constitute new matter or would require re-examination.

The exact page and line number where the errors occur in the application file are:

Page 1, paragraph 0002 in the Specification/Col. 1, line 24 in the issued patent.

Page 7, paragraph 0021 in the Specification/Col. 4, line 7 in the issued patent;


Page 7, paragraph 0022 in the Specification/Col. 4, line 23 in the issued patent.

Other errors listed on the Certificate of Correction form were apparently incurred through the fault of the PTO as will be disclosed by the records of files in the Office.

Attached hereto, in duplicate, is Form PTO-1050, with at least one copy being suitable for printing.

Respectfully submitted,

Dated: 5/30/07

By: 
David G. Latwesen, Ph.D.
Reg. No. 38,533

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : US 7,105,208 B2

ISSUED : September 12, 2006

APPLICATION NO.: 10/699,013

INVENTORS : Craig M. Carpenter

It is certified that an error or errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Col. 1, line 24 –

Replace “deposition (CVD) and atomic layer deposition (CVD). CVD”
With –deposition (CVD) and atomic layer deposition (ALD). CVD--

Col. 3, line 10 –

Replace “in the periodic table, namely, Al, Ga, In, Tl, Ge, Sn, Pb, Sb,”
With – in the periodic table, namely, Al, Ga, In, Tl, Ge, Sn, Pb, Sb,--

Col. 3, line 64 –

Replace “forming other than One monolayer at a time by stacking of”
With – forming other than one monolayer at a time by stacking of --

Col. 4, line 7 –

Replace “Traditional ALD can occur within an frequently-used”
With -- Traditional ALD can occur within frequently-used --

Col. 4, line 23 –

Replace “CVD is commonly used to form non-selectively a complete,”
With –CVD is commonly used to form non-selectively complete,”

Page
1 of 1

Mailing Address of Sender:

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